Impurity Doped UV Protection Layer

ABSTRACT OF THE DISCLOSURE

An ultra-violet (UV) protection layer is formed over a semiconductor workpiece before depositing a UV curable dielectric layer. The UV protection layer prevents UV light from reaching and damaging underlying material layers and electrical devices. The UV protection layer comprises a layer of silicon doped with an impurity, wherein the impurity comprises O, C, H, N, or combinations thereof. The UV protection layer may comprise SiOC:H, SiON, SiN, SiCO:H, combinations thereof, or multiple layers thereof, as examples.

(FIG. 1)